



## BUL49D

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- HIGH RUGGEDNESS

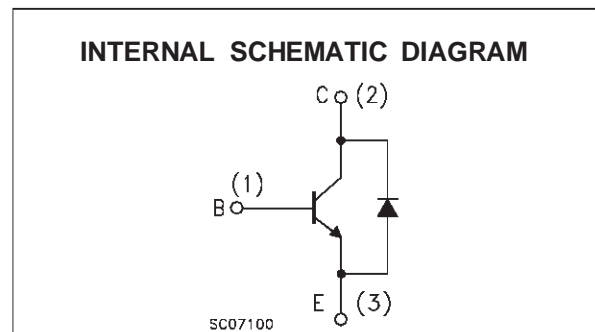
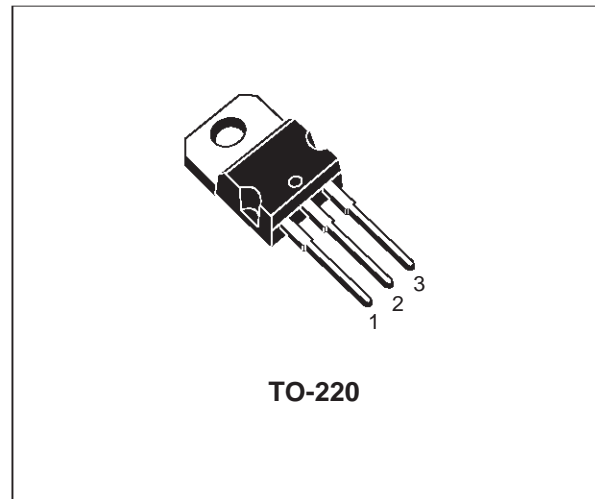
### APPLICATIONS

- ELECTRONIC TRANSFORMERS FOR HALOGEN LAMPS
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

### DESCRIPTION

The BUL49D is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and medium voltage capability.

The BUL49D is designed for use in electronic transformers for halogen lamps.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	850	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	450	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ , $I_B < 2.5$ A, $t_p < 10\mu s$ , $T_J < 150$ °C)	$BV_{EBO}$	V
$I_C$	Collector Current	5	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	10	A
$I_B$	Base Current	2	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	4	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	80	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_J$	Max. Operating Junction Temperature	150	°C

## BUL49D

### THERMAL DATA

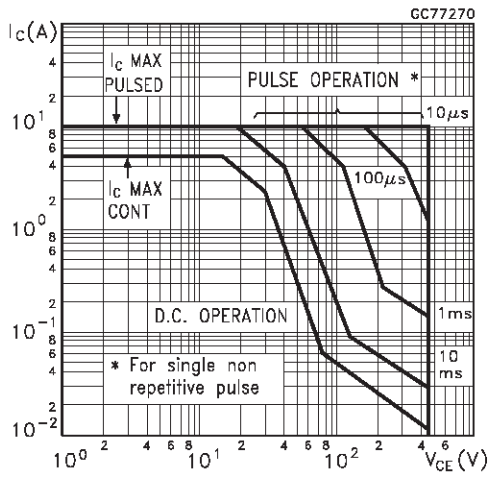
R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	1.56	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	62.5	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

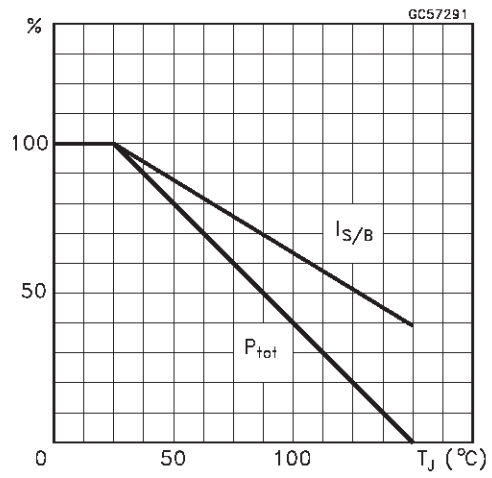
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 850 V V <sub>CE</sub> = 850 V T <sub>j</sub> = 125 °C			100 500	μA μA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 9 V			100	μA
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 10mA	10		18	V
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10 mA L = 25 mH	450			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A I <sub>C</sub> = 2 A I <sub>B</sub> = 0.4 A I <sub>C</sub> = 4 A I <sub>B</sub> = 0.8 A		0.1	0.3 0.6 1.2	V V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 0.2 A I <sub>C</sub> = 4 A I <sub>B</sub> = 0.8 A			1.0 1.3	V V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 10 mA V <sub>CE</sub> = 5 V I <sub>C</sub> = 0.5 A V <sub>CE</sub> = 5 V I <sub>C</sub> = 7 A V <sub>CE</sub> = 10 V	10 4		60 10	
V <sub>CEW</sub>	Maximum Collector Emitter Voltage Without Snubber	I <sub>C</sub> = 8 A R <sub>BB</sub> = 0 Ω V <sub>BB</sub> = -2.5 V L = 50μH t <sub>p</sub> = 10 μs	450			V
t <sub>s</sub> t <sub>f</sub>	RESISTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 2 A V <sub>CC</sub> = 250 V I <sub>B(on)</sub> = I <sub>B(off)</sub> = 0.4 A	2		3 0.8	μs μs
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 4 A I <sub>B(on)</sub> = 0.8 A V <sub>BE(off)</sub> = -5 V R <sub>BB</sub> = 0 Ω V <sub>CL</sub> = 300 V L = 1 mH		0.6 50	1.3 100	μs ns
V <sub>f</sub>	Diode Forward Voltage	I <sub>C</sub> = 3 A			1.5	V

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

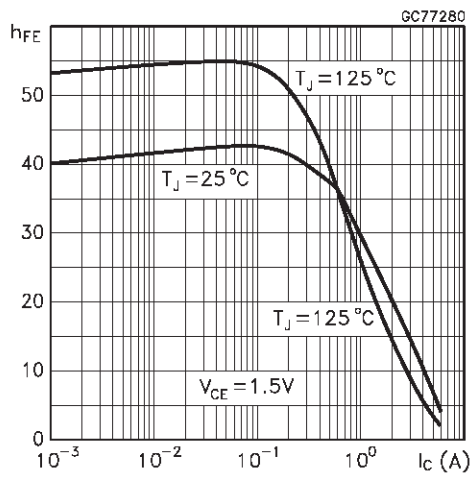
Safe Operating Areas



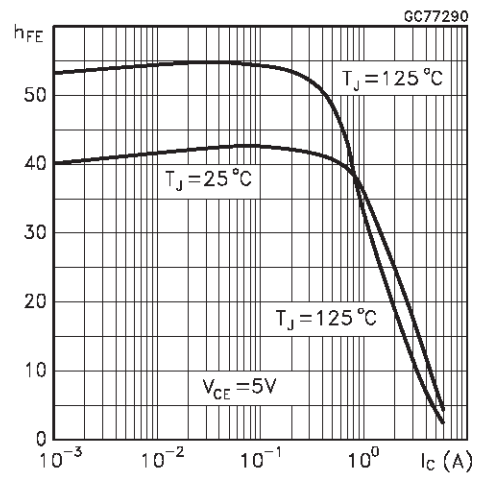
Derating Curve



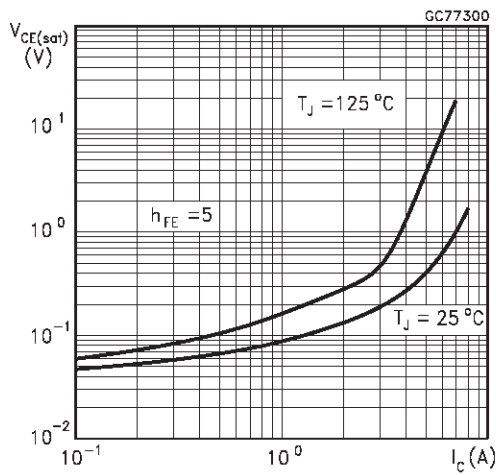
DC Current Gain



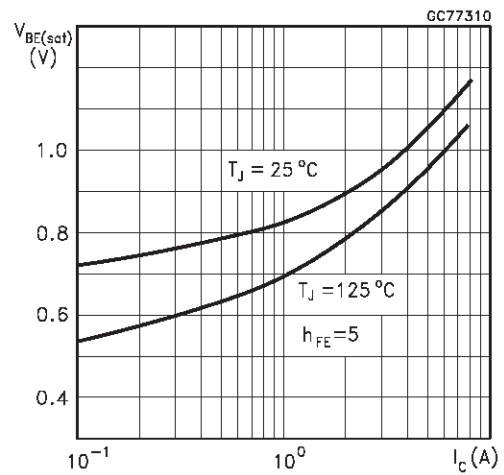
DC Current Gain



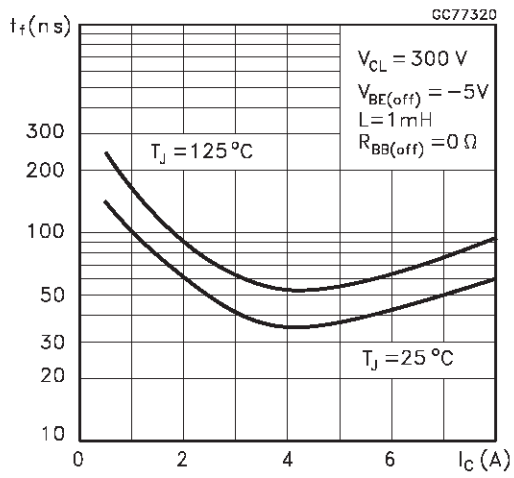
Collector Emitter Saturation Voltage



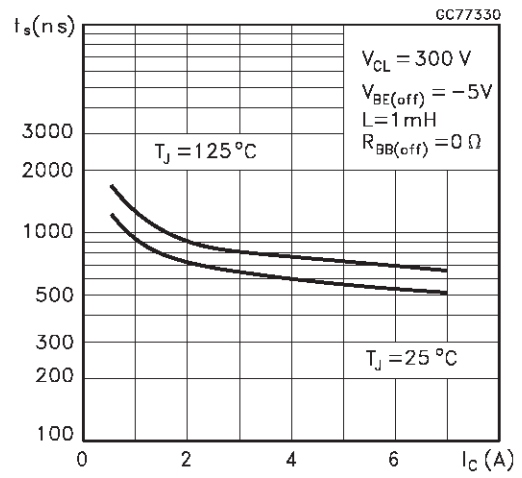
Base Emitter Saturation Voltage



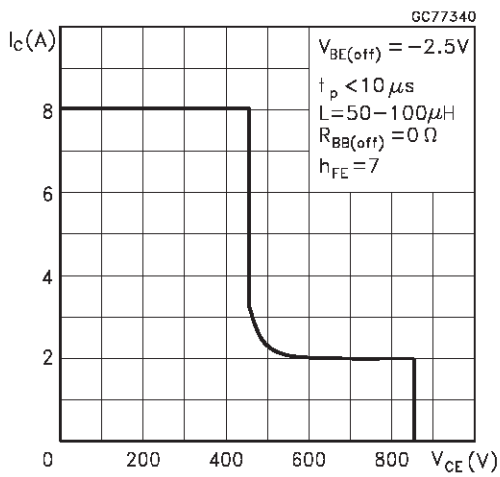
Inductive Fall Time



Inductive Storage Time

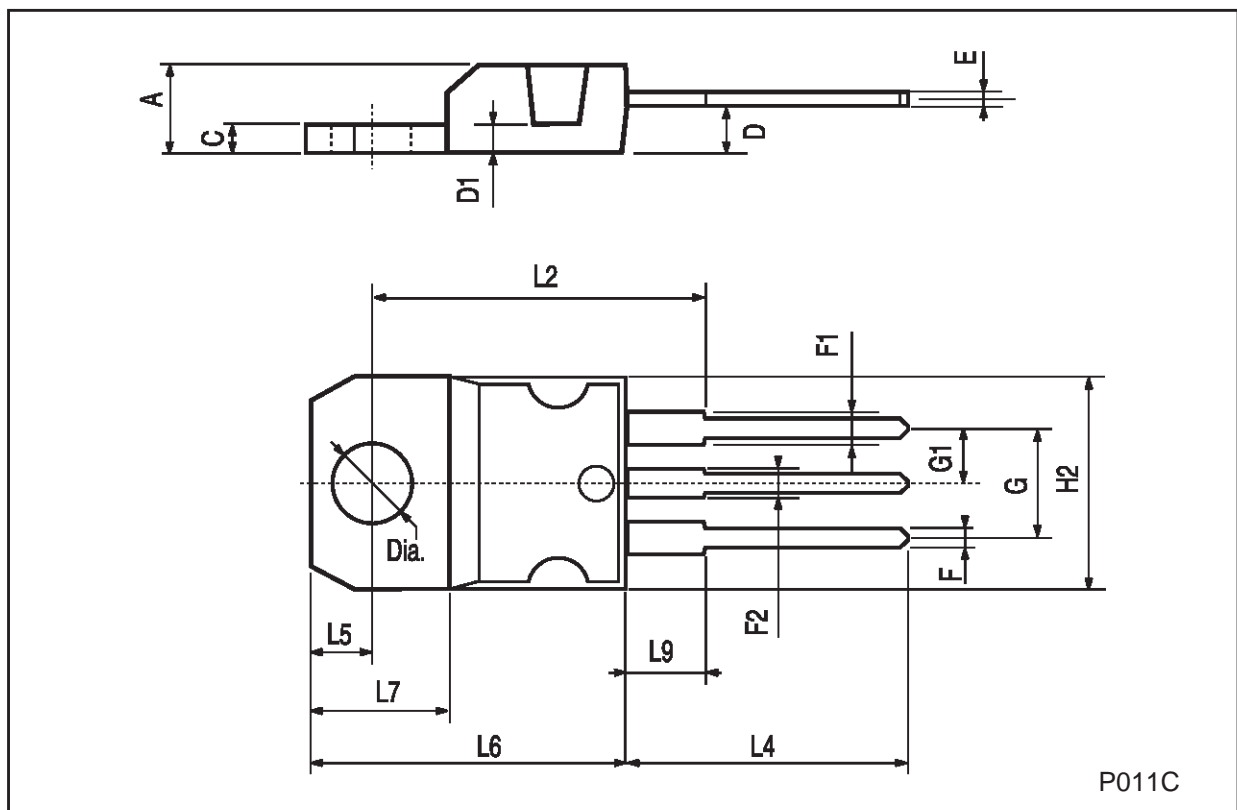


Reverse Biased SOA



**TO-220 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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